

60V N-Channel Planar Power MOSFET

• General Description

It combines planar MOSFET technology with a low resistance package to provide low $R_{DS(ON)}$.

• Features

- AEC-Q101 Qualified
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

• Application

- BLDC Motor driver
- DC-DC
- Battery protection

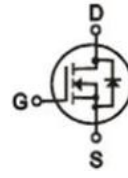
• Ordering Information:

Part NO.	ZMPA070N06HP
Marking	ZMP070N06H
Packing Information	TUBE
Basic ordering unit (pcs)	1000

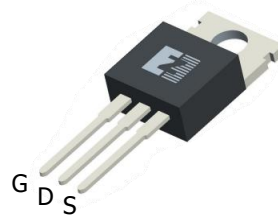
• Absolute Maximum Ratings ($T_C=25^{\circ}C$)

Parameter	Symbol	Conditions	Value	Unit
Drain-Source Voltage	V_{DS}		60	V
Gate-Source Voltage ^①	V_{GS}		± 20	V
Continuous Drain Current	I_D	$T_C=25^{\circ}C$	140	A
	I_D	$T_C=75^{\circ}C$	124	A
	I_D	$T_C=100^{\circ}C$	108	A
Pulsed Drain Current	I_{DM}	Pulsed; $t_p \leq 10 \mu s$; $T_{mb} = 25^{\circ}C$;	420	A
Total Power Dissipation	P_D	$T_C=25^{\circ}C$	300	W
Total Power Dissipation	P_D	$T_A=25^{\circ}C$	2.4	W
Operating Junction Temperature	T_J		-55 to +175	$^{\circ}C$
Storage Temperature	T_{STG}		-55 to +175	$^{\circ}C$
Single Pulse Avalanche Energy	E_{AS}	$L=0.5mH, V_{GS}=10V, R_g=25\Omega,$	1200	mJ
ESD Level (HBM)			CLASS 2	

• Product Summary



$V_{DS} = 60V$
 $R_{DS(ON)} = 4.5m\Omega$
 $I_D = 140A$



TO-220



•Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}		-	0.5	°C/W
Thermal resistance, junction-ambient	R_{thJA}		-	62	°C/W
Soldering temperature	T_{sold}		-	260	°C

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	60			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	2.0	2.6	4.0	V
Drain-Source Leakage Current	I_{DSS}	$V_{GS}=0V, V_{DS}=60V$			1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$			100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=20A$		4.5	7.0	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_{SD}=10A$		43		S
Diode Forward Voltage	V_{FSD}	$V_{GS}=0V, I_{SD}=20A$			1.3	V

•Dynamic characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Input capacitance	C_{iss}	$f=1MHz, V_{DS}=25V$	-	4980	-	pF
Output capacitance	C_{oss}		-	1290	-	
Reverse transfer capacitance	C_{rss}		-	435	-	
Gate Resistance	R_g	$f=1MHz$	-	1.4		Ω
Total gate charge	Q_g	$V_{DD}=15V, I_D=20A, V_{GS}=10V$	-	158	-	nC
Gate - Source charge	Q_{gs}		-	15	-	
Gate - Drain charge	Q_{gd}		-	52	-	
Turn-ON Delay time	$t_{D(on)}$	$V_{GS}=10V, V_{DS}=15V, R_G=3.3\Omega, I_D=20A$	-	22	-	ns
Turn-ON Rise time	t_r		-	76	-	ns
Turn-Off Delay time	$t_{D(off)}$		-	98	-	ns
Turn-Off Fall time	t_f		-	30	-	ns
Reverse Recovery Time	t_{RR}	$V_{DD}=20V, di_S/dt=100A/\mu s, I_S=50A$	-	98	-	ns
Reverse Recovery Charge	Q_{RR}		-	255	-	nC

Fig.1 Gate-Charge Characteristics

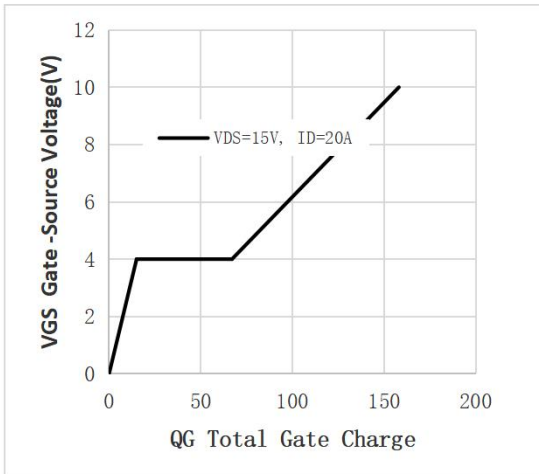


Fig.2 Capacitance Characteristics

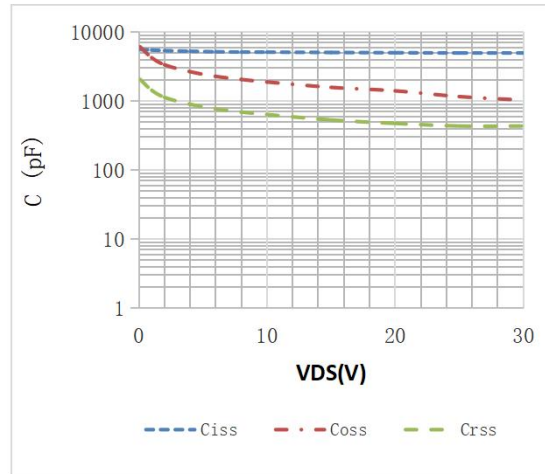


Fig.3 Power Dissipation

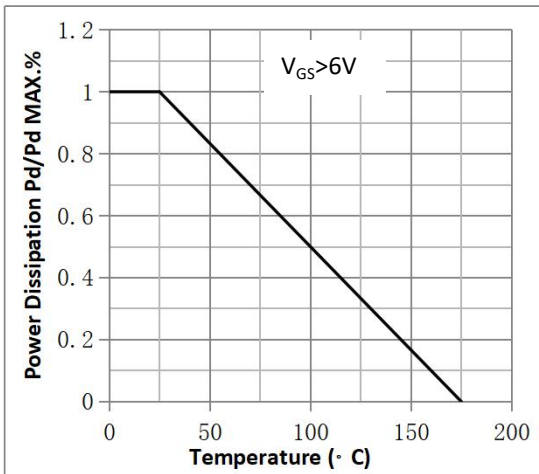


Fig.4 Typical output Characteristics

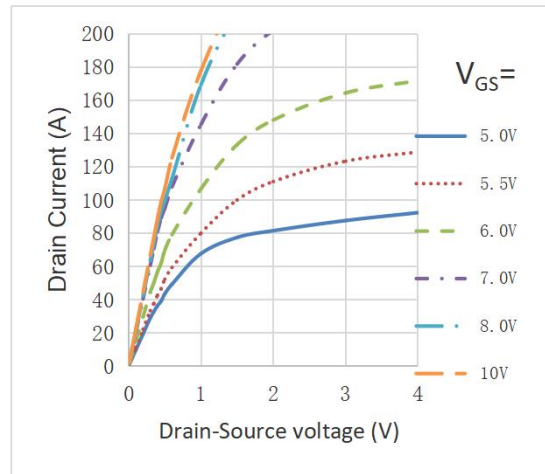


Fig.5 Threshold Voltage V.S Junction Temperature

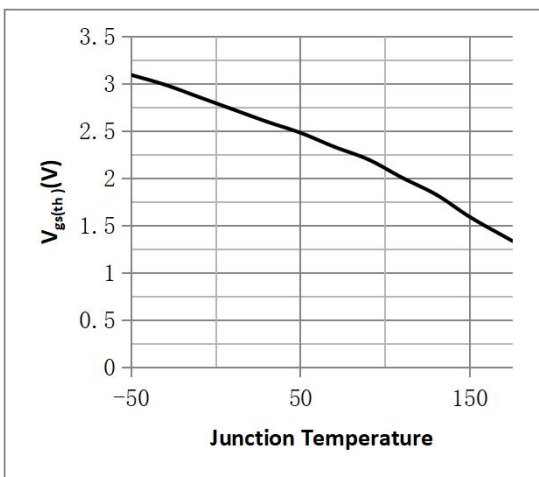


Fig.6 Resistance V.S Drain Current

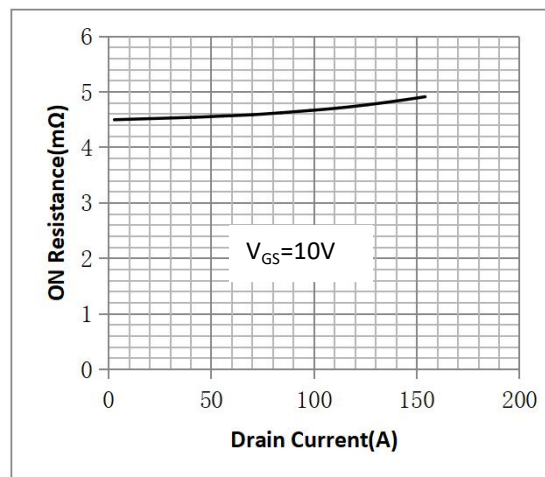


Fig.7 On-Resistance VS Gate Source Voltage

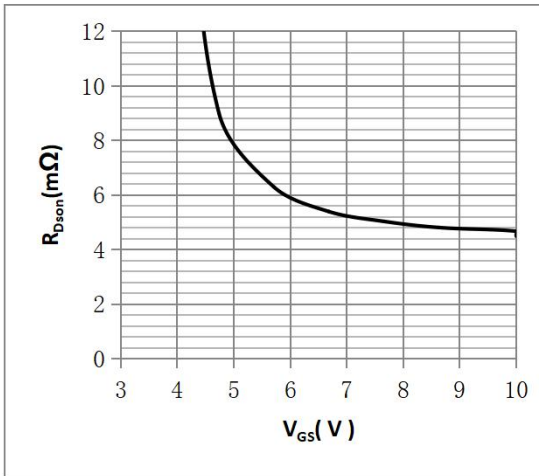


Fig.8 On-Resistance V.S Junction Temperature

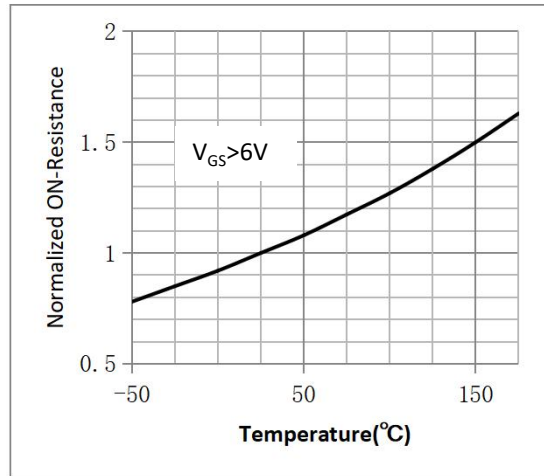


Figure 9. Diode Forward Voltage vs. Current

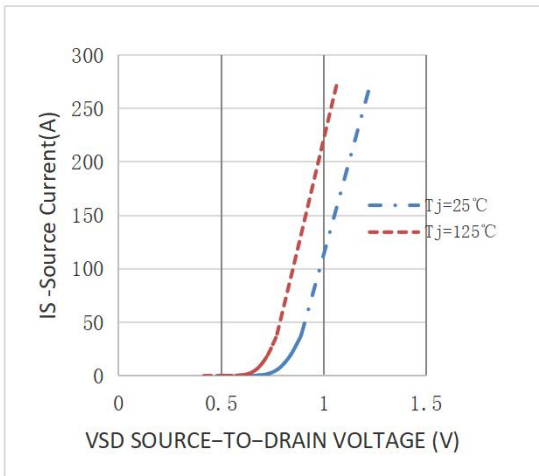


Figure 10. Transfer Characteristics

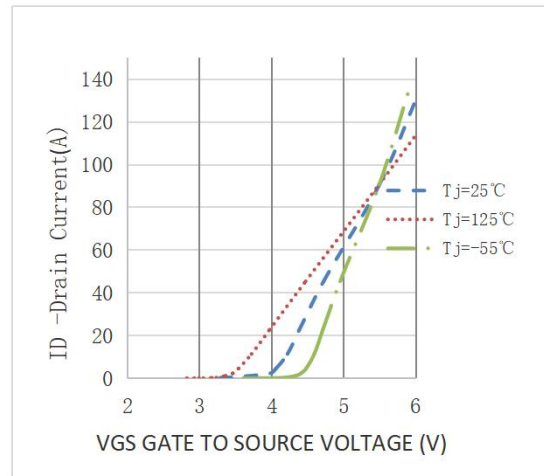


Fig.11 Safe Operating Area

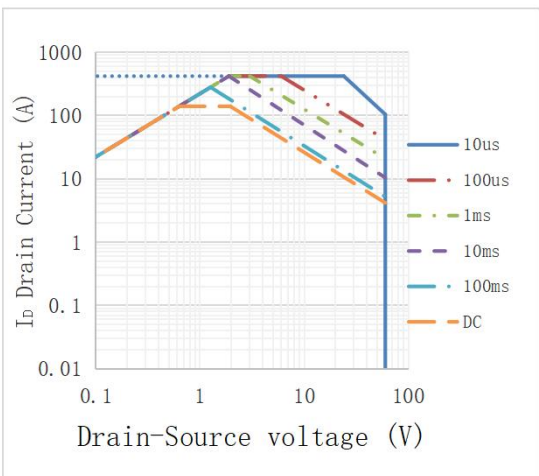
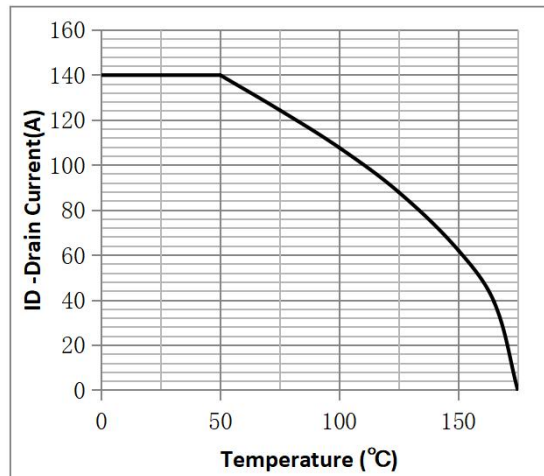
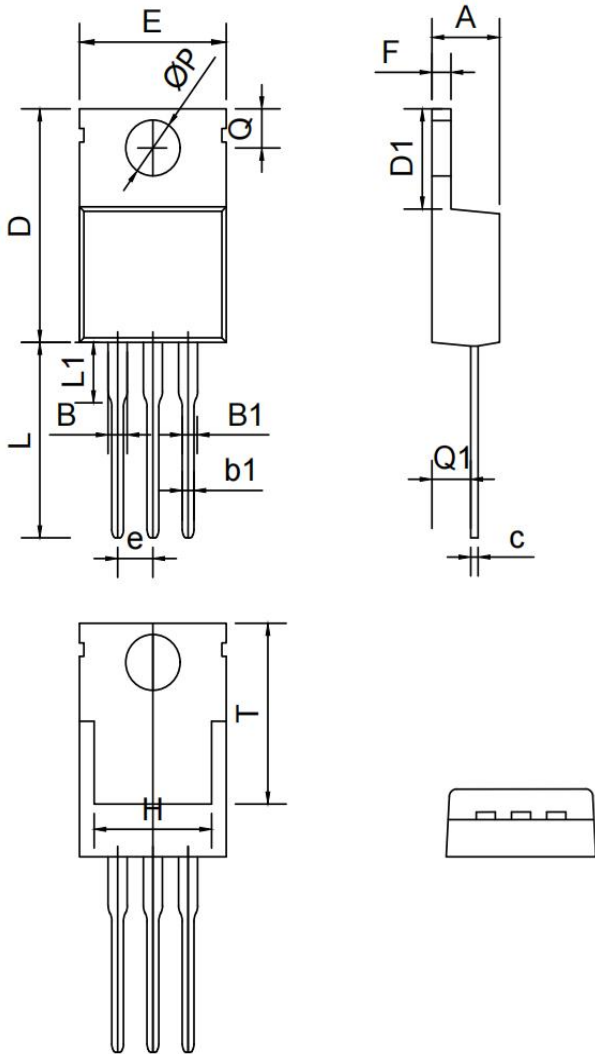


Fig.12 ID vs. Case Temperature^②



•TO-220 Package Outline



SYMBOLS	COMMON	
	MM	
	MIN.	MAX.
A	3.556	4.826
B	1.143	1.778
B1	1.000	1.450
b1	0.381	1.016
c	0.356	0.610
D	14.224	16.510
D1	5.842	6.858
E	9.652	10.668
e	2.340	2.740
F	0.508	1.400
L	12.600	14.732
L1	3.560	4.060
Q	2.500	3.048
Q1	2.032	2.921
ØP	3.600	3.900
T	12.042	12.878
H	6.858	8.890

Note:

① Pulse : $V_{GS}=+20V/-20V$, Duty cycle=50%, $T_j=175^\circ C$, $t=1000$ hours; For DC , the following test conditions can be passed: $V_{GS}=+20V/-10V$, $T_j=175^\circ C$, $t=1000$ hours;

② Practically the current will be limited by PCB, thermal design and operating temperature. $V_{GS}=10V$.

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Revision History

Version	Date	Change
A	2023.2.15	NEW
B	2023.9.19	Add Dynamic characteristics
C	2023.12.22	Correct Package Outline Dimension
D	2024.1.16	Adjust Figure 10. Transfer Characteristics